

## 1214-300M

300 Watts - 40 Volts, 150µs, 10% Radar 1200 - 1400 MHz

#### **GENERAL DESCRIPTION**

The 1214-300M is an internally matched, COMMON BASE transistor capable of providing 300 Watts of pulsed RF output power at one hundred fifty microseconds pulse width, ten percent duty factor across the band 1200 to 1400 MHz. This hermetically solder-sealed transistor is specifically designed for L-Band radar applications. It utilizes gold metalization and NiCr emitter ballasting to provide high reliability and supreme ruggedness.

#### ABSOLUTE MAXIMUM RATINGS

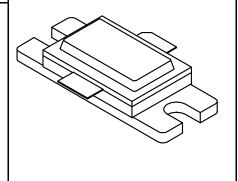
Maximum Power Dissipation @ 25°C 600 Watts

**Maximum Voltage and Current** 

BVces Collector to Emitter Voltage 70 Volts
BVebo Emitter to Base Voltage 3.5 Volts
Ic Collector Current 20 Amps

**Maximum Temperatures** 

Storage Temperature  $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature  $+200^{\circ}\text{C}$  CASE OUTLINE 55ST, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pg ŋc RI VSWR¹ VSWRs	Power Out Power Gain Collector Efficiency Input Return loss Load Mismatch Tolerance Load Mismatch - Stability	Freq = 1200 - 1400 MHz Vcc = 40 Volts Pin = 40 Watts Pulse Width = 150µs Duty Factor = 10%	300 8.75 50 10.0	55	2:1 1.5:1	Watts dB % dB

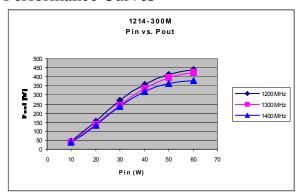
Note 1: Pulse condition of 150µsec, 10%.

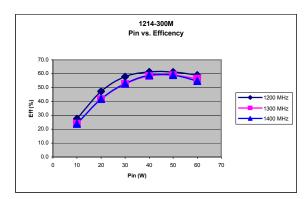
Bvces	Collector to Emitter Breakdown	Ic = 80  mA	70		Volts
Ices	Collector to Emitter Leakage	Vce = 40 Volts		10	mA
θjc¹	Thermal Resistance	Rated Pulse Condition		0.29	°C/W

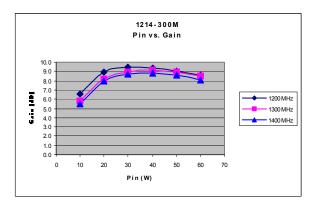


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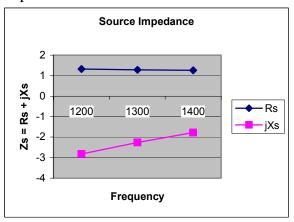
### Performance Curves

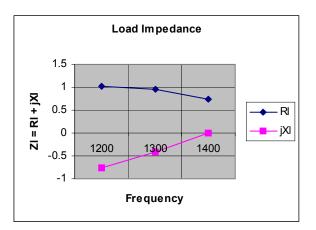




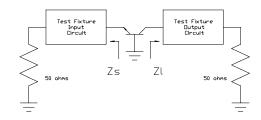


### Impedance Information





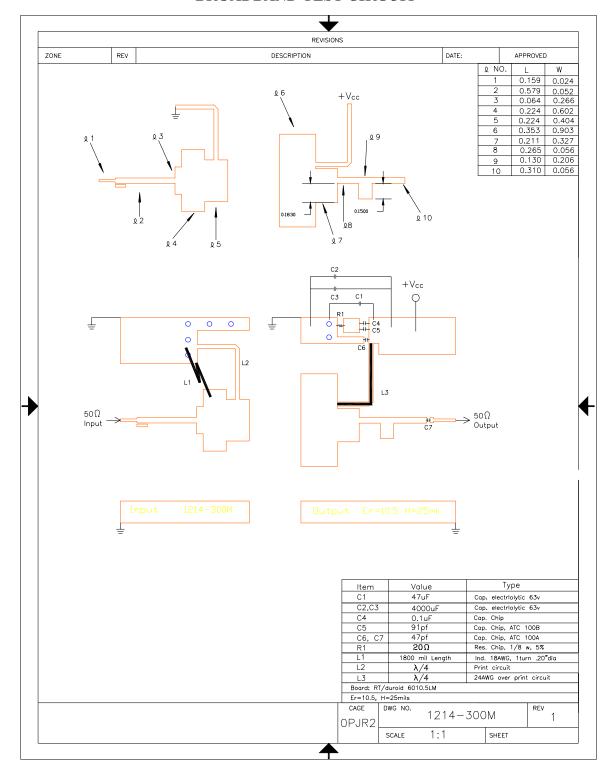
Impedance					
Freq	Zs	ZI			
1200	1.32-j2.82	1.03-j0.75			
1300	1.28-j2.26	0.95-j0.41			
1400	1.26-j1.78	0.75-j0.00			





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### **BROADBAND TEST CIRCUIT**





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